

**Silicon PNP Power Transistors****2SA634****DESCRIPTION**

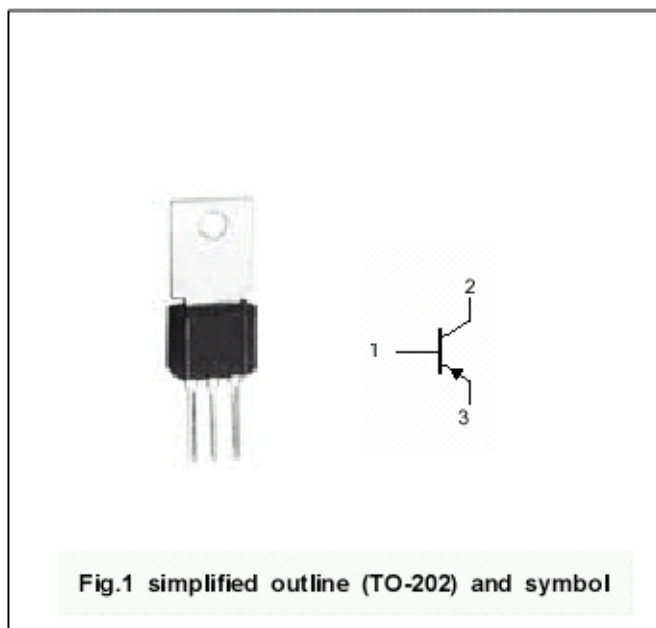
- With TO-202 package
- Complement to type 2SC1096
- High current capability

APPLICATIONS

- Audio frequency power amplifier
- Low speed switching

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

**Absolute maximum ratings ($T_a=25^{\circ}\text{C}$)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-40	V
V_{CEO}	Collector-emitter voltage	Open base	-30	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-3.0	A
I_{CM}	Collector current-peak		-6.0	A
I_B	Base current		-0.6	A
P_T	Total power dissipation	$T_a=25^{\circ}\text{C}$	1.2	W
		$T_c=25^{\circ}\text{C}$	10	
T_j	Junction temperature		150	$^{\circ}\text{C}$
T_{stg}	Storage temperature		-55~150	$^{\circ}\text{C}$



Silicon PNP Power Transistors

2SA634

CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEsat}	Collector-emitter saturation voltage	I _C =-3.0A ; I _B =-0.3 A			-2.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-3.0A ; I _B =-0.3 A			-2.0	V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA; I _B =0	-30			V
h _{FE-1}	DC current gain	I _C =-20mA ; V _{CE} =-5V	20			
h _{FE-2}	DC current gain	I _C =-1A ; V _{CE} =-5V	40		250	
I _{CBO}	Collector cut-off current	V _{CB} =-30V; I _E =0			-1.0	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =-3V; I _C =0			-1.0	μ A
C _{OB}	Output capacitance	I _E =0; V _{CB} =-10V; f=1MHz		75		pF
f _T	Transition frequency	I _C =-0.1A ; V _{CE} =-5V		55		MHz

◆ h_{FE-2} Classifications

N	M	L	K
40-60	50-100	80-160	120-250



PACKAGE OUTLINE

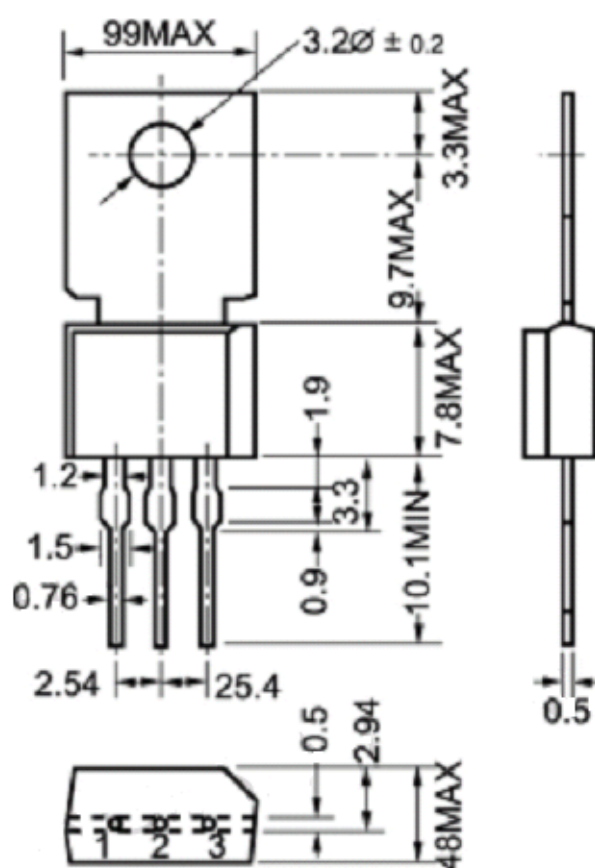


Fig.2 outline dimensions